

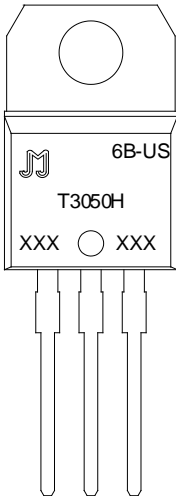
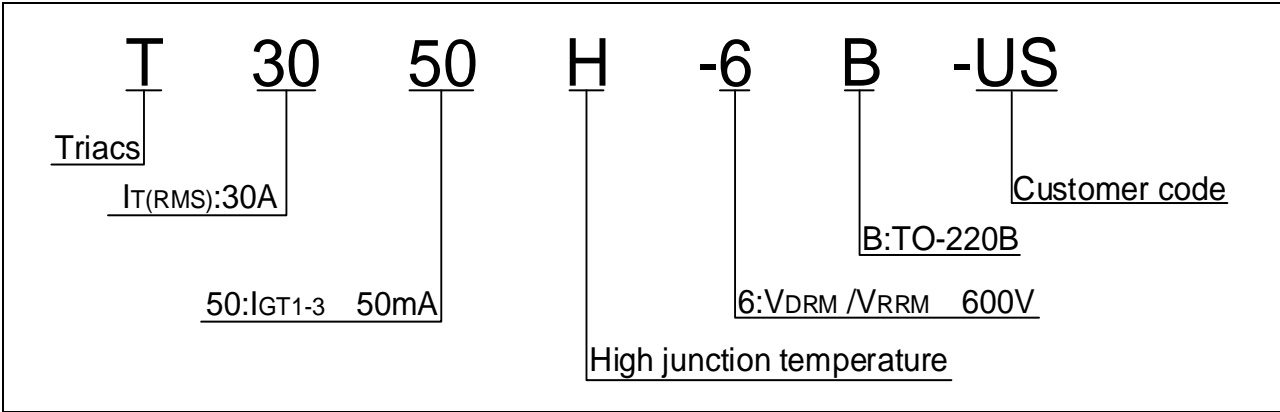
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	1.2	kV
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($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM} T_j=150$ $R_L=3.3K$	- -	MIN.	0.15	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	80	mA
				90	
I_H	$I_T=500mA$		MAX.	60	mA
dV/dt	$V_D=400V$ Gate Open $T_j=150$		MIN.	2200	V/ μs
(dI/dt) _c	(dV/dt) _c =20V/ μs , $T_j=150$		MIN.	30	A/ms
t_{on}	$I_G=80mA I_A=400mA I_R=40mA$ $T_j=25$		TYP.	15	μs
t_{off}				100	

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=42A t_p=380\mu s$	$T_j=25$	1.5	V
V_{TO}	Threshold voltage	$T_j=150$	0.7	V
R_D	Dynamic resistance	$T_j=150$	16	m
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=150$	5	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	0.75	W
$R_{th(j-a)}$	junction to ambient (AC)	60	W



XXX XXX

FIG.1 Maximum power dissipation versus RMS on-state current

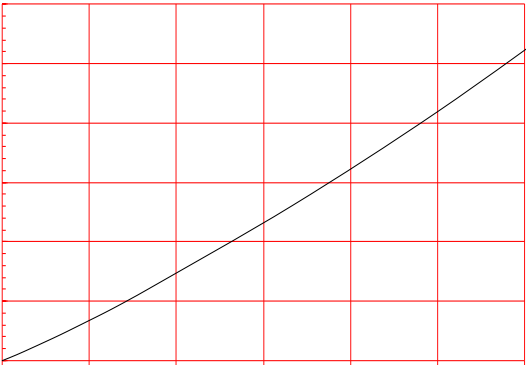


FIG.2: RMS on-state current versus case temperature

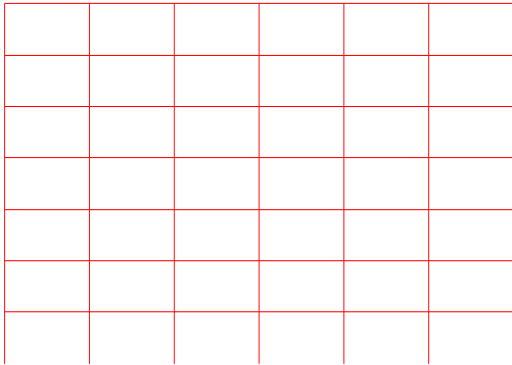
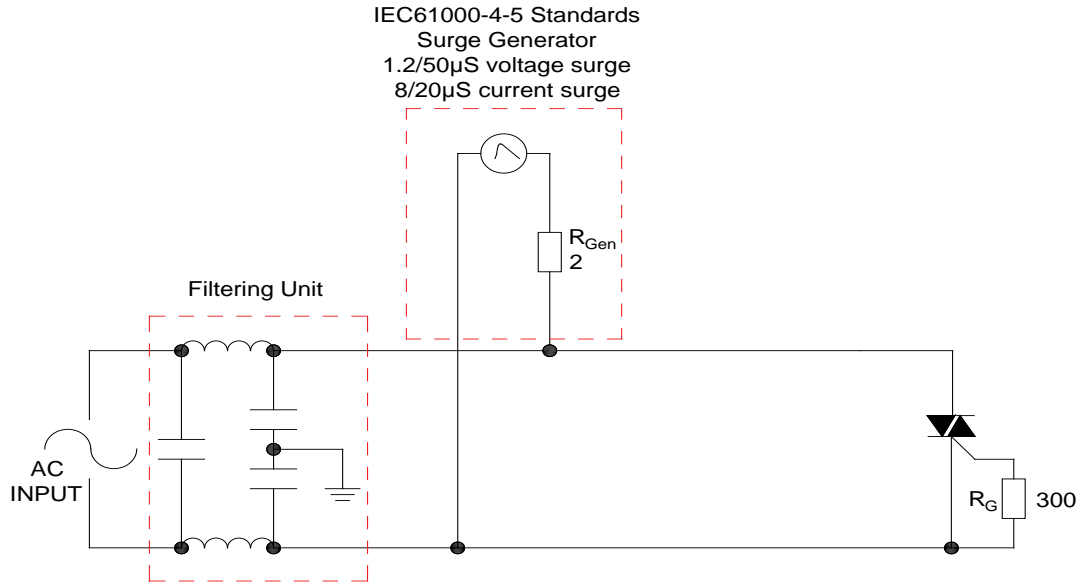


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards

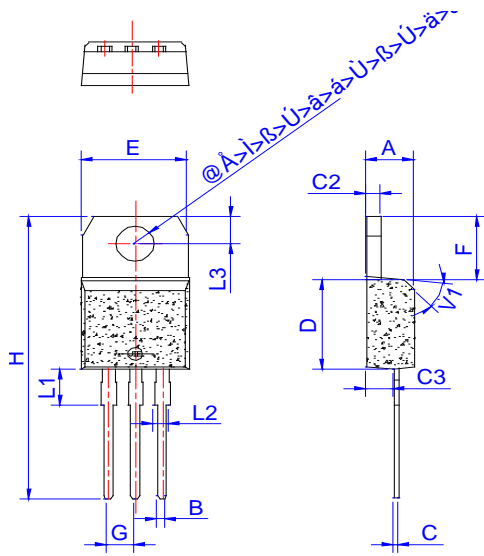


Refer to Instructions for installation of plastic-sealed in-line power devices released by JieJie

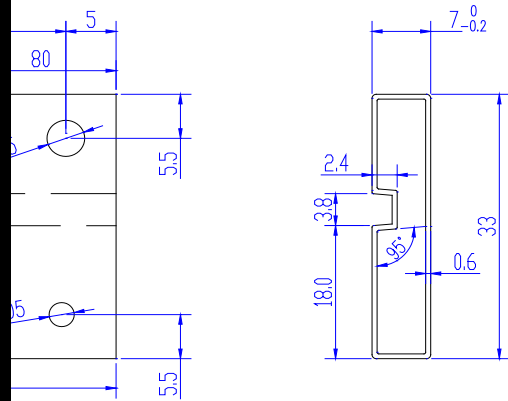
Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		H- I- J			
T3050H-6B-US	600	50	TO-220B	50	Tube

Document Revision History

Date	Revision	Changes
May.15, 2023	C-1	Last updated




Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	3.50		4.10	0.138		0.161
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	



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